



DMN62D0UWQ

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
60V	2Ω @ V _{GS} = 4.5V	340mA
000	2.5Ω @ V _{GS} = 2.5V	300mA

Description

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- **Power Management Functions**
- Backlighting

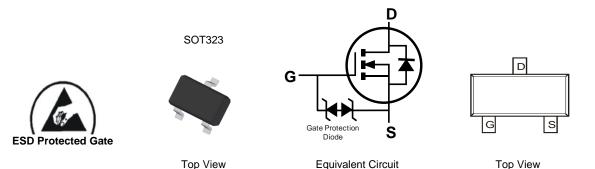
N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- 100% Rg Test in Production
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 @3)
- Weight: 0.006 grams (Approximate)



Ordering Information (Note 5)

	Part Number	Case	Packaging			
	DMN62D0UWQ-7	SOT323	3000/Tape & Reel			
	DMN62D0UWQ-13	SOT323	10000/Tape & Reel			
Notes:	1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

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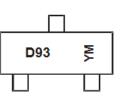
2. See https://www.diodes.com/guality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



D93= Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019)M = Month (ex: 9 = September)

Date Code Kev

	/											
Year	2018	3 20	19	2020	2021	2022	2023	202	4 2	025	2026	2027
Code	F	(3	Н		J	K	L		М	Ν	0
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V	
	Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$		ID	340 270	mA
Continuous Drain Current (Note 7) $V_{GS} = 4.5V$	t<5s	T _A = +25°C T _A = +70°C	ID	400 300	mA
Maximum Continuous Body Diode Forward Currer	nt (Note 7)	ls	0.4	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	%)	I _{DM}	1.2	А	
Pulsed Source Current (10µs Pulse, Duty Cycle =	1%)	I _{SM}	1.2	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		PD	320	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	398	°C/W
memai Resistance, Junction to Ambient (Note 6)	t<5s	R _{0JA}	306	C/W
Total Power Dissipation (Note 7)		PD	470	mW
Thermal Desistance, Junction to Ambient (Note 7)		Р	273	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	t<5s	R _{θJA}	235	C/VV
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	С°

Electrical Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60		_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	IDSS			1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}			±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						·
Gate Threshold Voltage	V _{GS(TH)}	0.5	—	1.0	V	$V_{DS} = 10V, I_D = 250\mu A$
			1.2	2.0		$V_{GS} = 4.5V, I_D = 0.1A$
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.4	2.5	Ω	V _{GS} = 2.5V, I _D = 0.05A
			1.8	3.0		V _{GS} = 1.8V, I _D = 0.05A
Forward Transconductance	Y _{fs}	-	1.8	_	S	V _{DS} =10V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	-	0.8	1.3	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 9)						·
Input Capacitance	Ciss	—	32	_	pF	
Output Capacitance	Coss	-	3.9	_	pF	V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	-	2.4	—	pF	1 = 1.000112
Gate Resistance	Rg	—	101	_	Ω	f = 1MHz , V _{GS} = 0V, V _{DS} = 0V
Total Gate Charge	Qq	—	0.5	—	nC	1 5 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
Gate-Source Charge	Q _{gs}	—	0.09		nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q _{qd}	—	0.09	—	nC	I _D = 250mA
Turn-On Delay Time	t _{D(ON)}	—	2.4	—	ns	
Turn-On Rise Time	t _R	—	2.5	—	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}	—	22.6	—	ns	$R_{G} = 25\Omega, I_{D} = 200 \text{mA}$
Turn-Off Fall Time	tF	—	12.5	—	ns	

Notes:

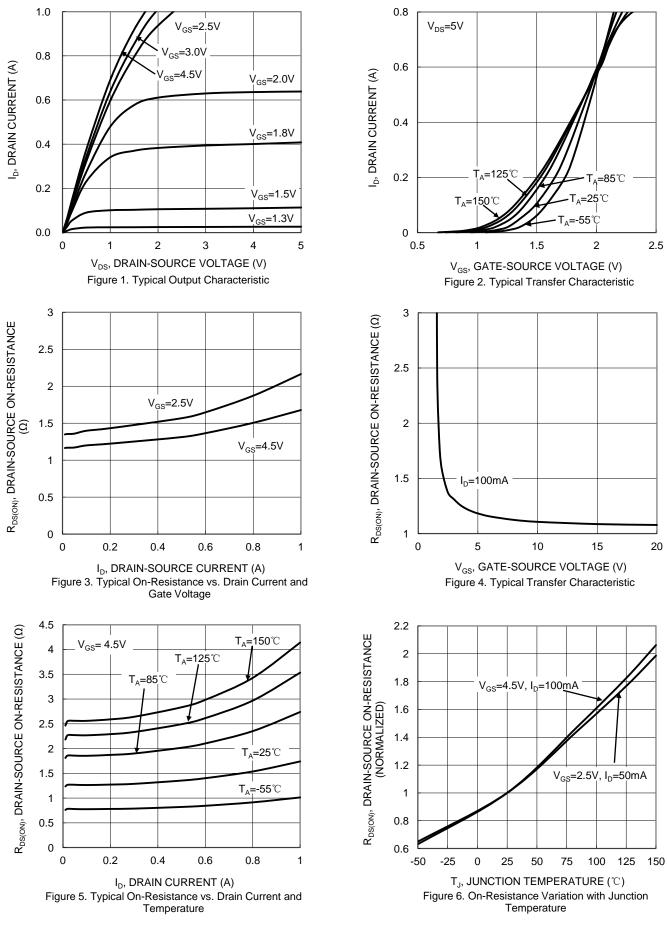
Device mounted on FR-4 PCB, with minimum recommended pad layout.
Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



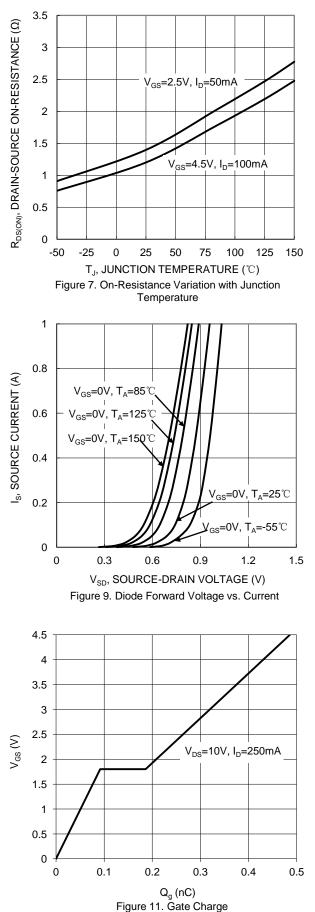
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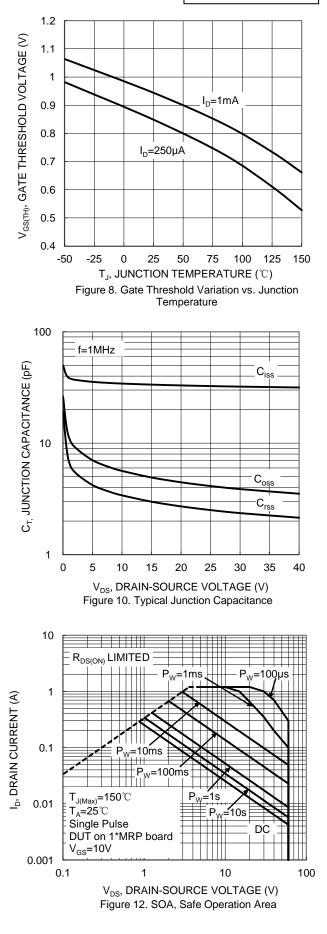


DMN62D0UWQ Document number: DS41502 Rev. 2 – 2 February 2019 © Diodes Incorporated



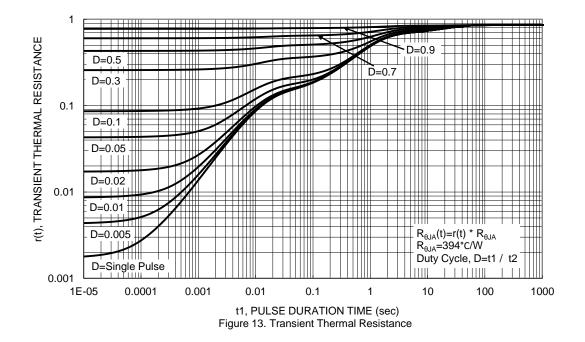






DMN62D0UWQ Document number: DS41502 Rev. 2 - 2 4 of 7 www.diodes.com



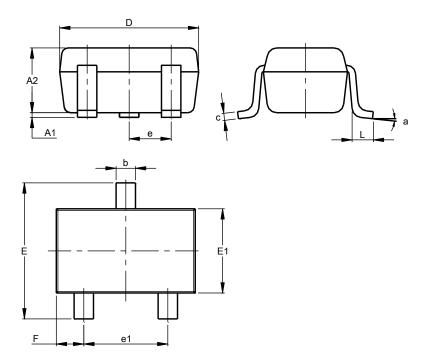




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

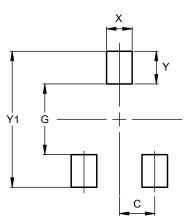
SOT323



SOT323								
Dim	Min Max Typ							
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
C	0.10	0.18	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C).650 B	SC					
e1	1.20	1.30						
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500

SOT323



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